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(54) Title: RADIO FREQUENCY SOURCE FOR INDUCTIVELY COUPLED AND CAPACITIVELY COUPLED PLASMAS IN
SUBSTRATE PROCESSING CHAMBERS

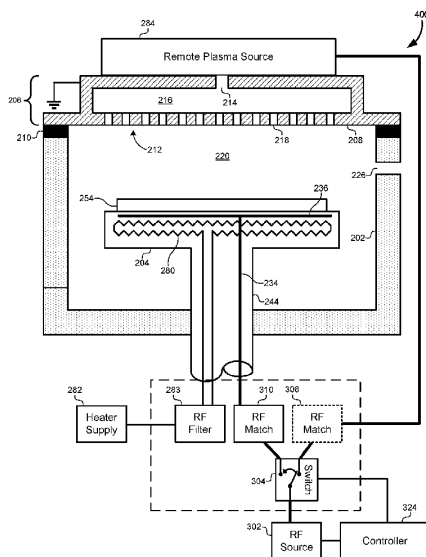


FIG. 4A

(57) Abstract: A radio frequency (RF) source may be used to generate a capacitively coupled plasma to perform a plasma-based process on a substrate in a plasma processing chamber. A controller may cause the RF source and a switching element to route an RF signal to electrodes in the pedestal that generate the plasma in the processing chamber as part of a recipe performed on a substrate during etch or deposition processes. Between processes, the controller may cause the same RF source to generate a second RF signal that is instead routed by the switching element to inductive coils to generate an inductively coupled plasma for a cleaning process to remove film deposits on the interior of the plasma processing chamber.

Declarations under Rule 4.17:

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